

TC74LCX02F/FN/FS

TENTATIVE DATA

LOW VOLTAGE QUAD 2-INPUT NOR GATE WITH 5V TOLERANT INPUTS AND OUTPUTS

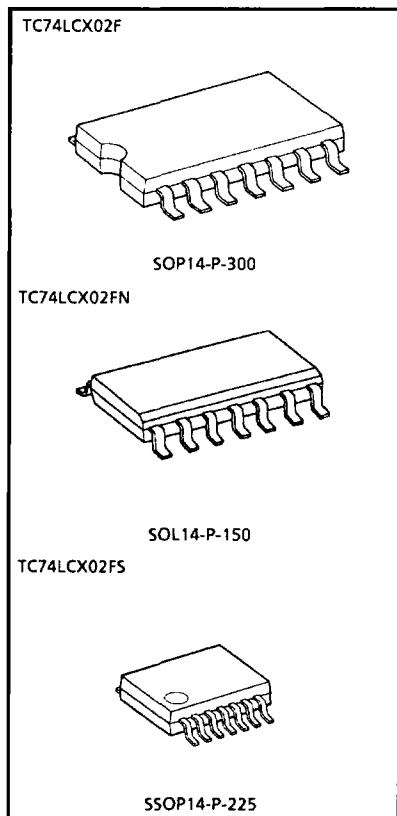
The TC74LCX02 is a high performance CMOS 2-INPUT NOR GATE. Designed for use in 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

The device is designed for low-voltage (3.3V) V_{CC} applications, but it could be used to interface to 5V supply environment for inputs.

All inputs are equipped with protection circuits against static discharge.

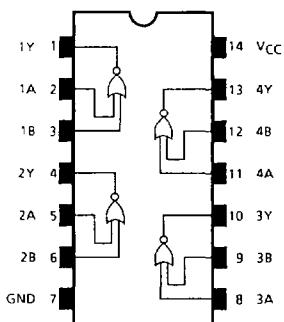
FEATURES

- Low voltage operation : $V_{CC} = 2.0 \sim 3.6V$
- High speed operation : $t_{pd} = 5.2\text{ns}$ (Max.)
($V_{CC} = 3.0 \sim 3.6V$)
- Output current : $|I_{OH}| / |I_{OL}| = 24\text{mA}$ (Min.)
($V_{CC} = 3.0V$)
- Latch-up performance : $\pm 500\text{mA}$
- Available in JEDEC SOP, EIAJ SOP and SSOP
- Power down protection is provided on all inputs and outputs.
- Pin and function compatible with the 74 series
(74AC/VHC/HC/F/ALS/LS etc.) 02 type.



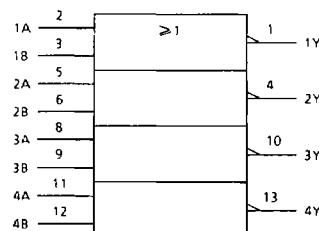
Weight SOP14-P-300 : 0.18g (Typ.)
 SOL14-P-150 : 0.12g (Typ.)
 SSOP14-P-225 : 0.07g (Typ.)

PIN ASSIGNMENT



(TOP VIEW)

IEC LOGIC SYMBOL



TRUTH TABLE

INPUTS		OUTPUTS
A	B	Y
L	L	H
L	H	L
H	L	L
H	H	L

MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Power Supply Voltage	V _{CC}	-0.5~7.0	V
DC Input Voltage	V _{IN}	-0.5~7.0	V
DC Output Voltage	V _{OUT}	-0.5~7.0 (Note 1)	V
		-0.5~V _{CC} + 0.5 (Note 2)	
Input Diode Current	I _{IK}	-50	mA
Output Diode Current	I _{OK}	±50 (Note 3)	mA
DC Output Current	I _{OUT}	±50	mA
Power Dissipation	P _D	180	mW
DC V _{CC} /Ground Current	I _{CC} /I _{GND}	±100	mA
Storage Temperature	T _{stg}	-65~150	°C

(Note 1) V_{CC} = 0V(Note 2) High or Low State. I_{OUT} absolute maximum rating must be observed.(Note 3) V_{OUT} < GND, V_{OUT} > V_{CC}

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	2.0~3.6	V
		1.5~3.6 (Note 4)	
Input Voltage	V_{IN}	0~5.5	V
		0~5.5 (Note 5)	
Output Voltage	V_{OUT}	0~ V_{CC} (Note 6)	V
		± 24 (Note 7)	
Output Current	I_{OH}/I_{OL}	± 12 (Note 8)	mA
		—	
Operating Temperature	T_{opr}	-40~85	°C
Input Rise And Fall Time	dt/dv	0~10 (Note 9)	ns/V

(Note 4) Data Retention Only

(Note 5) $V_{CC} = 0V$

(Note 6) High or Low State

(Note 7) $V_{CC} = 3.0\sim 3.6V$ (Note 8) $V_{CC} = 2.7\sim 3.0V$ (Note 9) $V_{IN} = 0.8\sim 2.0V$, $V_{CC} = 3.0V$

ELECTRICAL CHARACTERISTICS

DC characteristics ($T_a = -40\sim 85^\circ C$)

PARAMETER		SYMBOL	TEST CONDITION		V_{CC} (V)	MIN.	MAX.	UNIT	
Input Voltage	"H" Level	V_{IH}	$V_{IN} = V_{IL}$	$I_{OH} = -100\mu A$	2.7~3.6	2.0	—	V	
	"L" Level	V_{IL}			2.7~3.6	—	0.8		
Output Voltage	"H" Level	V_{OH}	$V_{IN} = V_{IL}$	$I_{OH} = -100\mu A$	2.7~3.6	$V_{CC} - 0.2$	—	V	
				$I_{OH} = -12mA$	2.7	2.2	—		
				$I_{OH} = -18mA$	3.0	2.4	—		
				$I_{OH} = -24mA$	3.0	2.2	—		
	"L" Level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100\mu A$	2.7~3.6	—	0.2	V	
				$I_{OL} = 12mA$	2.7	—	0.4		
				$I_{OL} = 16mA$	3.0	—	0.4		
				$I_{OL} = 24mA$	3.0	—	0.55		
Input Leakage Current	I_{IN}	$V_{IN} = 0\sim 5.5V$		2.7~3.6		—	± 5.0	μA	
Power Off Leakage Current	I_{OFF}	$V_{IN}/V_{OUT} = 5.5V$		0		—	10.0	μA	
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND		2.7~3.6		—	10.0	μA	
		$V_{IN}/V_{OUT} = 3.6\sim 5.5V$		2.7~3.6		—	± 10.0		
Increase In I_{CC} Per Input	ΔI_{CC}	$V_{IH} = V_{CC} - 0.6V$		2.7~3.6		—	500	μA	

AC characteristics ($T_a = -40\sim85^\circ C$)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	MIN.	MAX.	UNIT
Propagation Delay Time	t_{pLH}	(Fig.1, 2)	2.7	—	6.0	ns
	t_{pHL}		3.3 ± 0.3	1.5	5.2	
Output To Output Skew	t_{osLH}	(Note 10)	2.7	—	—	ns
	t_{osHL}		3.3 ± 0.3	—	1.0	

(Note 10) Parameter guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$$

DYNAMIC SWITCHING CHARACTERISTICS ($T_a = 25^\circ C$, Input $t_r = t_f = 2.5\text{ ns}$, $C_L = 50\text{ pF}$, $R_L = 500\Omega$)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	TYP	UNIT
Quiet Output Maximum Dynamic VOL	V_{OLP}	$V_{IH} = 3.3V, V_{IL} = 0V$	3.3	TBD	V
Quiet Output Minimum Dynamic VOL	$ V_{OLV} $	$V_{IH} = 3.3V, V_{IL} = 0V$	3.3	TBD	V

CAPACITIVE CHARACTERISTICS ($T_a = 25^\circ C$)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	TYP	UNIT	
Input Capacitance	C_{IN}	—	3.3	TBD	pF	
Power Dissipation Capacitance	C_{PD}	$f_{IN} = 10\text{ MHz}$	(Note 11)	3.3	TBD	pF

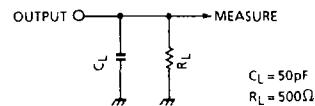
(Note 11) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(\text{opr.})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4 \text{ (Per gate)}$$

TEST CIRCUIT

Fig.1



AC WAVEFORM

Fig.2 t_{pLH} , t_{pHL}

